L Number	Hits	Search Text	DB	Time stamp
	659		USPAT;	2003/05/01 09:46
			US-PGPUB	
_	141	((216/2).CCLS.) and (void or release or	USPAT;	2003/05/27 13:27
	1.4.1	cavity) and silicon adj dioxide	US-PGPUB	2000,00,2, 10.2
_	70		USPAT;	2003/05/01 10:02
		cavity) and MEMS	US-PGPUB	2003/03/01 10:02
_	264		USPAT;	2003/04/29 09:27
_	264	((216/2).CCLS.) and silicon adj dioxide		2003/04/29 09:27
	F 1 7	mong and granificial and (seed to	US-PGPUB	1 3003/05/30 00 00
_	51/	mems and sacrificial and (cavity or void)	USPAT;	2003/05/30 09:02
			US-PGPUB	0000/04/00 10 54
_	7	mems and sacrificial and (cavity or void)	DERWENT	2003/04/29 12:54
T	33		DERWENT	2003/04/30 12:00
_	2	mems and sacrificial	JPO	2003/04/29 12:59
-	4	mems and (void or cavity)	JPO	2003/04/29 12:59
-	109	1 · · · · · · · · · · · · · · · · · · ·	USPAT;	2003/04/29 14:25
		(substrate or silicon)).clm.	US-PGPUB	
-	22	sacrificial and (wafer near3 bond\$3)	DERWENT	2003/04/30 12:10
-	1	release and silicon and dioxide and (wafer	DERWENT	2003/04/30 12:08
		near3 bond\$3)		
_	4		DERWENT	2003/04/30 12:09
		and silicon and dioxide and (substrate		
		near3 bond\$3)		
<u>y</u> 11	708		USPAT;	2003/04/30 12:11
	/08	Sacrificial and (water Hears Donass)	US-PGPUB	2000/04/30 12:11
	300	granificial and (information hands)		2003/05/30 10:12
7	366	· · · · · · · · · · · · · · · · · · ·	USPAT;	2003/05/30 10:12
		(silicon adj dioxide) and (releas\$3 or	US-PGPUB	
		etch\$3)	.,,,,,,	0000/01/00
_	5	(sacrificial and (wafer near3 bond\$3) and	USPAT;	2003/04/30 12:14
		(silicon adj dioxide) and (releas\$3 or	US-PGPUB	
		etch\$3)).clm.		
_	195	(sacrificial and (wafer near3 bond\$3) and	USPAT;	2003/04/30 12:15
		mems)	US-PGPUB	
_	3	(("6417743") or ("6463339") or	USPAT;	2003/05/01 09:52
		("6348788")).PN.	US-PGPUB	
	1	("6159385").PN.	USPAT;	2003/05/01 10:00
			US-PGPUB	
_	1	("6417743").PN.	USPAT;	2003/05/01 10:00
		(0,11,7,10 / 1,114 .	US-PGPUB	2000,00,01 10.00
_	1 2	((216/2).CCLS.) and (void or release or	USPAT;	2003/05/01 10:02
	12			2003/03/01 10:02
	7.0	cavity) and MEM	US-PGPUB	2002/05/01 10:02
_	/9	((216/2).CCLS.) and (void or release or	USPAT;	2003/05/01 10:03
	<u> </u>	cavity) and (MEM or "MEM's")	US-PGPUB	0000 /05 /07 /07
-	240		USPAT;	2003/05/27 13:40
		cavity or well) and silicon adj dioxide	US-PGPUB	
-	215	((216/2).CCLS.) and (micromechanical or	USPAT;	2003/05/27 14:03
į		MEMS or micro-electromechanical or	US-PGPUB	
		microelectromechanical)		
	1009	(micromechanical or MEMS or	USPAT;	2003/05/30 10:03
		micro-electromechanical or	US-PGPUB	
		microelectromechanical or		
		micro-mechanical).ti.		
_	1039		USPAT;	2003/05/27 14:07
	1000	micro-electromechanical or	US-PGPUB	2003/03/2/ 14.0/
		micro-erectromechanical or microelectromechanical	US FGEOD	
		microelectromechanical or		
	07.	micro-mechanical).ti.	II C D T C	2002/05/20 10 05
-	8 / 4	(micromechanical or MEMS or	USPAT;	2003/05/30 10:07
	0.17	micro-electromechanical or	US-PGPUB	
		microelectromechanical		
		micro-electro-mechanical or		
		micro-mechanical).ti. and (cavity or void		
	Ma.	or recess or well)		
_	49	(mems and (cavity or void or recess)).ab.	USPAT;	2003/05/30 09:03
			US-PGPUB	
_	195	(microstructures or MEMS).ti. and (void or	USPAT;	2003/05/30 09:48
		cavity or recess)	US-PGPUB	
	9		USPAT	2003/05/30 09:41
_		"5543013" "5637539" "5747353"		2000,00,00
-			,	
	3 75 ·	"5824177" "5879963" "6020215").PN.	IICDAT.	2003/05/20 00-52
_	325		USPAT; US-PGPUB	2003/05/30 09:52

			· · ·	1 6000 105 100 000 5
_	59	method same suspended same structure? same silicon	USPAT; US-PGPUB	2003/05/30 09:54
_	1269	(micromechanical or MEMS or	USPAT;	2003/05/30 10:04
	1200	microstructure? or micro-electromechanical	US-PGPUB	
		or microelectromechanical or		
		micro-mechanical).ti.		
-	89	(micromechanical or MEMS or	JPO	2003/05/30 10:04
		microstructure? or micro-electromechanical		
		or microelectromechanical or		
		micro-mechanical).ti.		
_	149		USPAT;	2003/05/30 10:09
		micro-electromechanical or	US-PGPUB	
		microelectromechanical		
		micro-electro-mechanical or micro-mechanical or microstructures or		
		microstructure or suspended).ti. and		
		(cavity or void or recess or well) and		
		MEMS and wafer and silicon		
_	701	(wafer same (silicon adj \$20xide) same	USPAT;	2003/05/30 10:37
		etch\$3) and (micromechanical or mems or	US-PGPUB	
		microstructure? or micro-mechanical)		
_	4	("5578976" "5585311" "5646432"	USPAT	2003/05/30 10:34
		"5658698").PN.		
_	82	(sealed adj cavity) same (wafer or	USPAT;	2003/06/02 17:09
		substrate) same (\$2oxide or dielectric or	US-PGPUB	
		insulat\$3)		
-	235		USPAT;	2003/06/02 16:08
		(structure or mechanical or etch\$3)	US-PGPUB	
_	1	"6465355"	DERWENT	2003/06/02 16:02
-	2627	2003-310327.NRAN.	DERWENT	2003/06/02 16:02
_	2637	cavity and suspended and (structure or mechanical or micromachin\$3) and etch\$3	USPAT; US-PGPUB	2003/06/02 16:24
	62		USPAT;	2003/06/02 16:23
	02	(cavity and micromachings):ab. and etches	US-PGPUB	2003/00/02 10.23
_	3	(void and micromachin\$3).ab. and etch\$3	USPAT;	2003/06/02 16:23
. ((voia and mioromaoning) vasi and ocomy	US-PGPUB	
_	365	void and micromachin\$3 and etch\$3	USPAT;	2003/06/02 16:42
			US-PGPUB	
_	54	(cavity and suspended and (structure or	USPAT;	2003/06/02 16:25
		mechanical or micromachin\$3)).ab.	US-PGPUB	
_	5	svoronos.in.	USPAT;	2003/06/02 16:43
	0.1.0		US-PGPUB	0000 (00 10 15 15
_	213	(harris adj richard).in.	USPAT;	2003/06/02 16:47
_	35	(krotschmann) in	US-PGPUB	2003/06/02 16:47
-	35	(kretschmann).in.	USPAT; US-PGPUB	2003/00/02 10:4/
_	4163	MEMS and (remov\$3 or etch\$3)	USPAT;	2003/06/02 17:00
	100	india (temovyo et ecenyo)	US-PGPUB	2000/02 17.00
_	111	(mems and (void or cavity) and (substrate	USPAT;	2003/06/02 17:00
		or silicon)).clm.	US-PGPUB	
-	393	(438/48).CCLS.	USPAT;	2003/06/02 17:45
			US-PGPUB	
-	79	((438/48).CCLS.) and (cavity or void or	USPAT;	2003/06/02 17:14
		recess)	US-PGPUB	
-	302	(438/52).CCLS.	USPAT;	2003/06/02 18:03
			US-PGPUB	
-	186	(438/51).CCLS.	USPAT;	2003/06/02 18:13
	1.54	///20/51)	US-PGPUB	2002/06/02 10 0:
-	154	((438/51).CCLS.) not ((438/52).CCLS.)	USPAT;	2003/06/02 18:04
_	152	(438/456).CCLS.	US-PGPUB	2003/06/02 18:14
_	132	(430/430).CCL3.	USPAT; US-PGPUB	2003/00/02 18:14
_	591	(438/455).CCLS.	USPAT;	2003/06/02 18:15
		(150) 150) . CCED.	US-PGPUB	2000/00/02 10.13
	548	((438/455).CCLS.) not ((438/456).CCLS.)	USPAT;	2003/06/02 18:16
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB	
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